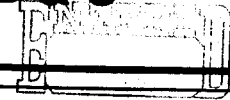




# SOLID STATE DEVICES, INC

14849 Firestone Boulevard · La Mirada, CA 90638  
Phone: (714) 670-SSDI (7734) · Fax: (714) 522-7424

## SXM33B thru SXM63B & C

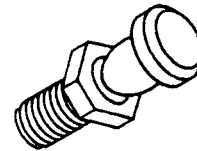
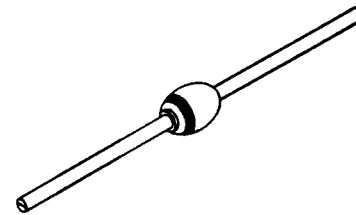


The SXM Series is constructed from a single chip metallurgically bonded both sides. The series provide large chip area for high power applications when higher junction capacitance is acceptable). The high reverse voltage ratings allow operation with large swing RF signals.

### PIN DIODE SERIES

### RF POWER SWITCH AND ATTENUATOR

#### CASE STYLE B



CASE STYLE C

## Designer's Data Sheet

### FEATURES:

- Operating Frequency up to 3GHz
- Voltage Ratings to 3000 Volts
- Power Dissipation to 40 Watts Continuous
- 500kW Peak Pulse Power Dissipation
- For RF Switches and Attenuator Applications
- Long Carrier Life Time Design
- Various Intrinsic Region Lengths Available
- Axial, Surface Mount and Ministud Versions
- Custom Design Upon Request
- Screening to TX, TXV and Space Levels

### AVERAGE POWER RATINGS

RATING		SYMBOL	SXM33	SXM43	SXM63	UNIT
			VALUE			
Power Dissipation	Add "B" Suffix (note 1)	PD	1.0	12	15	Watts
	Add "B" Suffix (note 2)		0.4	2.5	4	
	Add "C" Suffix		---	25	40	
Thermal Resistance	Add "B" Suffix (note 1)	RθJL	60	75	75	°C/W
	Add "B" Suffix (note 2)	RθJL	---	---	---	
	Add "C" Suffix	RθJC	25	37.5	37.5	
Peak Power Dissipation		PPD	75	250	500	kW
Operating & Storage Temperature		Top & Tstg	-65 to +175			°C

### NOTES:

- 1) 1/2" total length to 25°C contact/derate linearly to 175°C for TL>25°C  
Free Air

NOTE: All specifications are subject to change without notification. SCD's for these devices should be reviewed by SSDI prior to release.

DATA SHEET #: RP0035 A

RMD

HIGH FREQUENCY

# SXM33B thru SXM63B & C



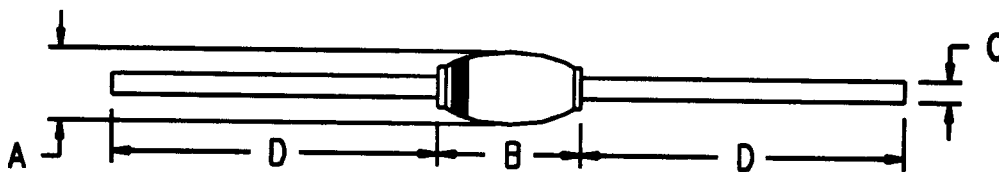
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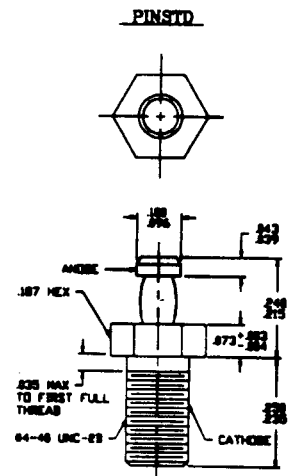
ELECTRICAL CHARACTERISTICS		SXM33		SXM43		SXM63		
CHARACTERISTICS	SYMBOL	MIN	MAX	MIN	MAX	MIN	MAX	UNIT
Reverse Breakdown Voltage (at 10mA)	BVR	---	2500	---	2500	---	2000	V
Forward Voltage Drop (at IF = 1 Amp)	VF	---	1.7	---	1.2	---	0.9	V
Reverse Leakage Current (at VR = 300 Volts)	IR	---	200	---	200	---	200	nA
Junction Capacitance (VR = 100 Volts, 1 MHz)	CJ	0.3	0.7	1.25	1.70	3.5	4.5	pF
Carrier Lifetime (at IF = 10mA)	$\tau$	5.0	---	5.0	---	5.0	---	$\mu$ sec
Intrinsic Region Width	W	150	---	150	---	150	---	$\mu$ m
Series Resistance (IF = 100mA, 100 MHz) (IF = 10 $\mu$ A, 100 MHz)	Rs	1.7(typ) ---	2.5 5	0.7(typ) ---	1 3	0.5(typ) ---	0.8 1	$\Omega$ K $\Omega$
RF Parallel Resistance (VR=100Volts, 100 MHz)	Rp	10(typ)	---	10(typ)	---	7(typ)	---	K $\Omega$

## CASE OUTLINE:

### CASE B



### CASE C



DIMENSIONS: SXM33			DIMENSIONS: SXM43			DIMENSIONS: SXM63		
DIM	MIN.	MAX.	DIM	MIN.	MAX.	DIM	MIN.	MAX.
A	---	.100"	A	---	.135"	A	---	.160"
B	---	.225"	B	---	.200"	B	---	.200"
C	.016"	.020"	C	.025"	.032"	C	.036"	.040"
D	1.0"	---	D	1.0"	---	D	1.0"	---